

Claims

- [c1] A method for forming a structure for testing external connections to semiconductor devices, the method comprising:
- providing a thin film of electrically insulating material;
 - providing a plurality of passages through the thin film of electrically insulating material, wherein the passages are arranged in a pattern corresponding to a pattern of external connections on the semiconductor device;
 - providing electrically conducting material in the plurality of passages; and
 - providing electrical connections between the electrically conducting material in selected passages.
- [c2] The method according to claim 1, wherein providing the electrical connections between the electrically conducting material in the selected passages comprises providing electrically conducting material on the thin film of electrically insulating material between the selected passages.
- [c3] The method according to claim 1, wherein the selected passages are adjacent pairs.

- [c4] The method according to claim 1, wherein the electrical connections are provided between a plurality of passages.
- [c5] The method according to claim 1, wherein the electrical connections are provided between non-adjacent passages